



DMP4025SFGQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C (Note 7)
-40V	25mΩ @ V _{GS} = -10V	- 7.2A
-40V	$45 \mathrm{m}\Omega @ \mathrm{V}_{\mathrm{GS}} = -4.5 \mathrm{V}$	- 5.4A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- **DC-DC Converters**
- Printer Equipment

40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Features

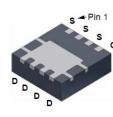
- Low R_{DS(ON)} Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

Mechanical Data

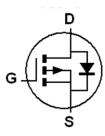
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.0172 grams (Approximate)



Top View



Bottom View



Device Symbol

Ordering Information (Note 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel	
DMP4025SFGQ-7	P40	7	8	2,000	
DMP4025SFGQ-13	P40	13	8	3,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



P40 = Product Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-40	V
Gate-Source Voltage		V _{GSS}	±20	V
	(Note 7)		-7.2	
Continuous Drain Current, V _{GS} = -10V	$T_A = +70^{\circ}C$ (Note 7)	ID	-5.77	
	(Note 6)		-4.65	
Maximum Body Diode Forward Current	(Note 7)	Is	-7.2	A
Pulsed Drain Current	(Note 8)	I _{DM}	-80	
Pulsed Source Current	(Note 8)	I _{SM}	-80	

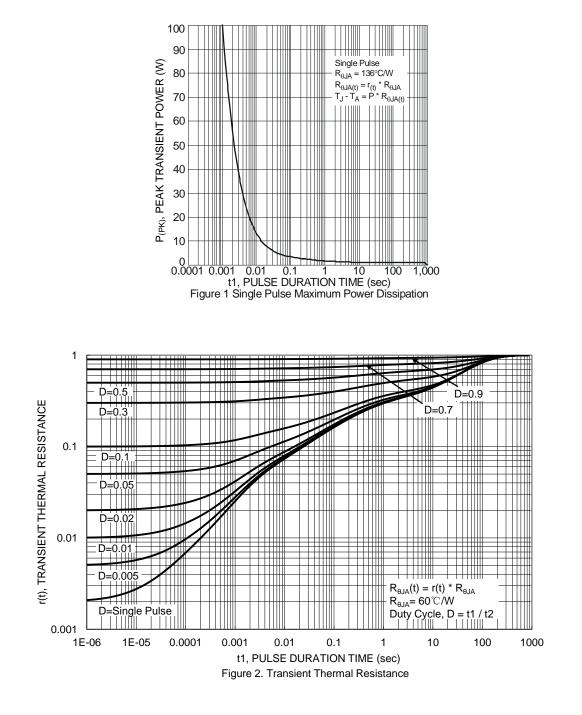
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	P	0.81	W	
Linear Derating Factor	(Note 7)	P _D	1.95	٧V	
Thermal Resistance, Junction to Ambient	(Note 6)	D	155	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	64		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
For a device surface mounted on 25mm x 25mm FR-4 PCB with 2oz copper, in still air conditions.
Same as note (7), except the device is pulsed with D= 0.02 and pulse width 300µs. Notes:



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

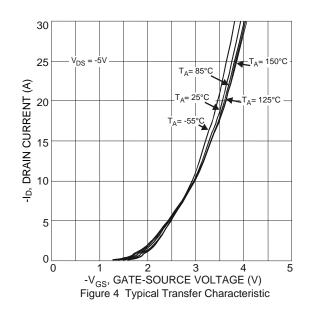
Characteristic	Cumple of	M.:	Turn	Max	L lus it	Test Condition	
	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS				1			
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—		V	$I_{D} = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}		—	-1.0	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-0.8	-1.3	-1.8	V	$I_D = -250\mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D		18	25	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Drain-Source On-Resistance (Note 9)	R _{DS(ON)}	_	30	45	11122	$V_{GS} = -4.5V, I_D = -3A$	
Forward Transconductance (Notes 9 & 10)	g fs	_	16.6		S	$V_{DS} = -5V, I_D = -3A$	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.7	-1.0	V	$I_{S} = -1A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1643				
Output Capacitance	Coss	_	179		pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	128				
Gate Resistance	R _g	_	6.43		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (Note 11)	Qg	_	14.0			$V_{GS} = -4.5V$	
Total Gate Charge (Note 11)	Qg	_	33.7		nC	V _{DS} = -20V	
Gate-Source Charge (Note 11)	Q _{gs}	_	5.5		nc	$V_{GS} = -10V$ $I_D = -3A$	
Gate-Drain Charge (Note 11)	Q _{qd}		7.3				
Turn-On Delay Time (Note 11)	t _{D(ON)}	_	6.9			·	
Turn-On Rise Time (Note 11)	t _R	_	14.7		n 0	$V_{DD} = -20V, V_{GS} = -10V$	
Turn-Off Delay Time (Note 11)	t _{D(OFF)}		53.7		ns	I _D = -3A	
Turn-Off Fall Time (Note 11)	t _F	_	30.9				

Notes:

Typical Characteristics

9. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.

30 V_{GS} = -10V V_{GS} = -4.5V /_{GS} = 4.0V 25 -I_D, DRAIN CURRENT (A) 20 ∨_{GS} = -3.5∨ 15 -V_{GS} = -3.0V-10 5 V_{GS} = -2.5V $V_{GS} = -2.0V V_{GS} = -2.2V$ 0 0.5 1 1.5 -V_{DS}, DRAIN-SOURCE VOLTAGE (V) 2 0 Figure 3 Typical Output Characteristic





DMP4025SFGQ

T_A= 1[']50°C

T_A= 125°C

T_A= 85°C

 $T_A = 25^{\circ}C$

T_A= -55°C

25

30

20

_-4.5V

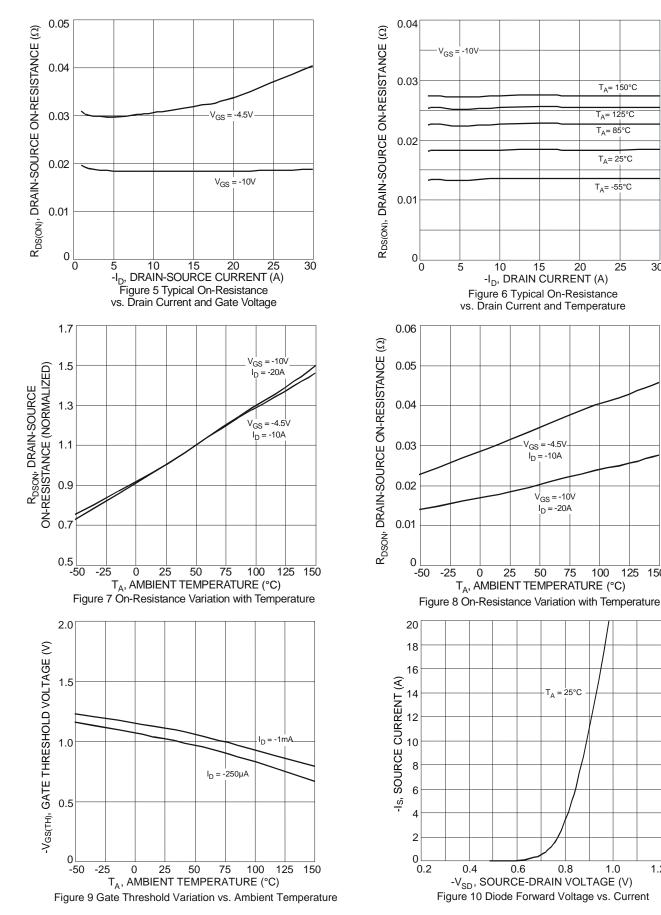
75

T_A = 25°C

0.8

1.0

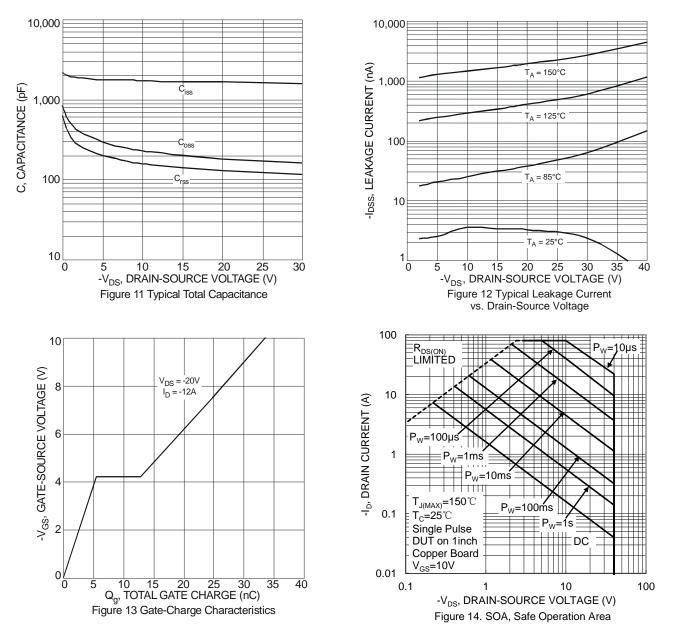
100 125 150



1.2



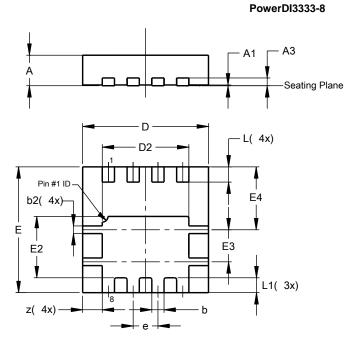
DMP4025SFGQ





Package Outline Dimensions

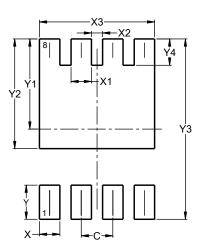
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	-	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	-	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8

Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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